

ABSTRACT

The measurement of the width of a pattern on a semiconductor wafer or a flat panel is carried out in an optical microscope or a scanning electron microscope in a number of measuring steps, By a computing rule, the quality of the correlation between the measured data obtained in the individual measurement steps, as well as reference data
5 taken from the design, the value for the parameter is calculated and compared with a limiting value obtained from experience. In the event of violation of the limiting value, a signal is generated and the further processing of the object is interrupted.